



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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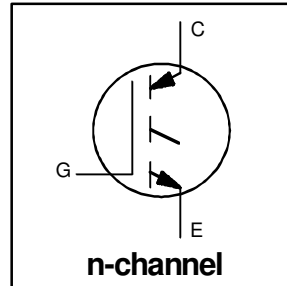
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### Features

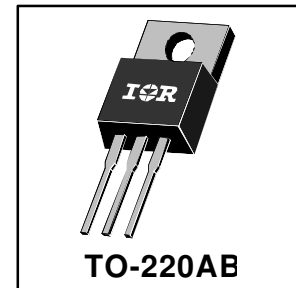
- Switching-loss rating includes all "tail" losses
- Optimized for line frequency operation (to 400 Hz)  
See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 600V$
$V_{CE(sat)} \leq 1.8V$
@ $V_{GE} = 15V, I_C = 31A$

### Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	50	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	31	
$I_{CM}$	Pulsed Collector Current ①	240	
$I_{LM}$	Clamped Inductive Load Current ②	100	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$E_{ARV}$	Reverse Voltage Avalanche Energy ③	15	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	160	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	65	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.77	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
$Wt$	Weight	—	2.0 (0.07)	—	g (oz)

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

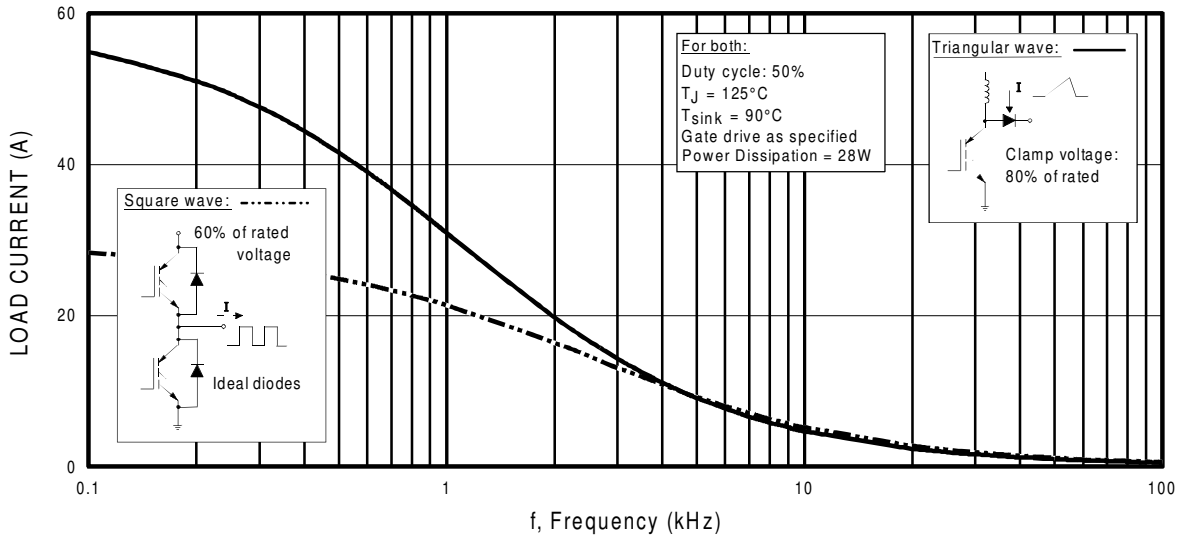
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coeff. of Breakdown Voltage	—	0.75	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.6	1.8	V	$I_C = 31A$ $I_C = 60A$ $I_C = 31A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig. 2, 5
		—	2.2	—		
		—	1.7	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temp. Coeff. of Threshold Voltage	—	-9.3	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance ⑤	12	21	—	S	$V_{CE} = 100V, I_C = 31A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

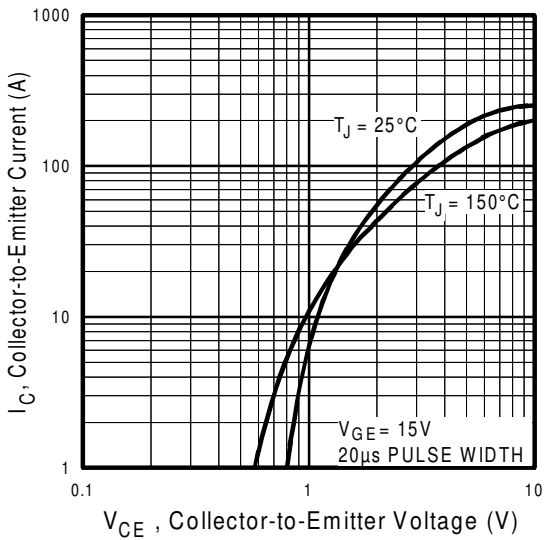
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	62	90	nC	$I_C = 31A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig. 8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	10	15		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	27	40		
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 31A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail"
$t_r$	Rise Time	—	50	—		
$t_{d(off)}$	Turn-Off Delay Time	—	1100	1500		
$t_f$	Fall Time	—	620	1100		
$E_{on}$	Turn-On Switching Loss	—	1.0	—		
$E_{off}$	Turn-Off Switching Loss	—	12	—	mJ	See Fig. 9, 10, 11, 14
$E_{ts}$	Total Switching Loss	—	13	20		
$t_{d(on)}$	Turn-On Delay Time	—	29	—		
$t_r$	Rise Time	—	53	—	ns	$T_J = 150^\circ\text{C}$ , $I_C = 31A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail"
$t_{d(off)}$	Turn-Off Delay Time	—	1600	—		
$t_f$	Fall Time	—	1200	—		
$E_{ts}$	Total Switching Loss	—	22	—		
$L_E$	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	1600	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{oes}$	Output Capacitance	—	140	—		
$C_{res}$	Reverse Transfer Capacitance	—	20	—		

### Notes:

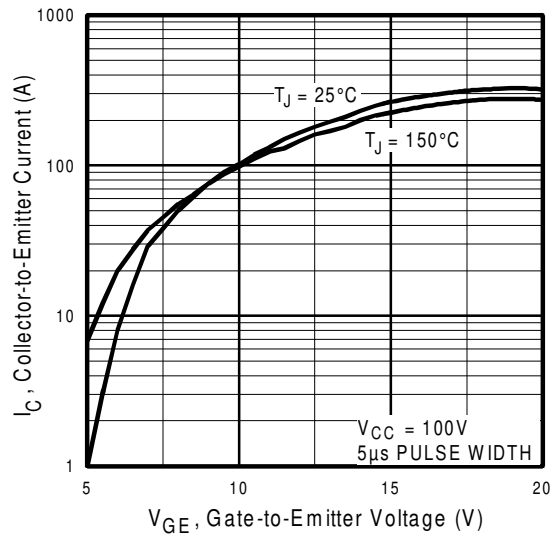
- ① Repetitive rating;  $V_{GE}=20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC}=80\%(V_{CES}), V_{GE}=20V, L=10\mu H, R_G=10\Omega$ , ( See fig. 13a )
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.



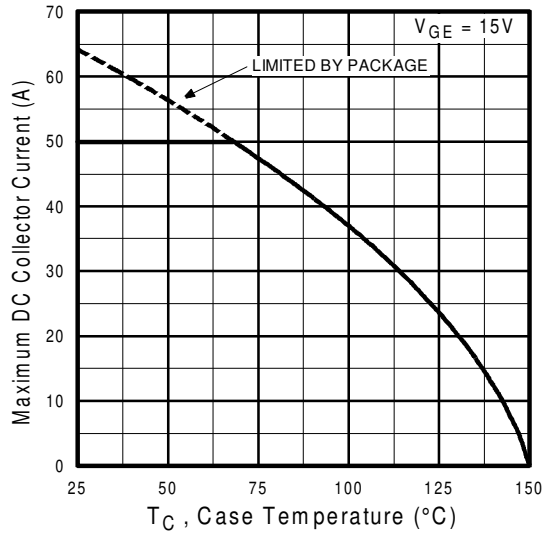
**Fig. 1 - Typical Load Current vs. Frequency**  
 (For square wave,  $I = I_{RMS}$  of fundamental; for triangular wave,  $I = I_{PK}$ )



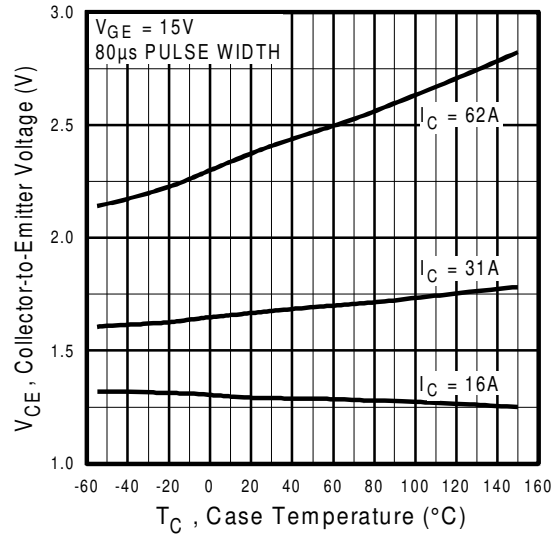
**Fig. 2 - Typical Output Characteristics**



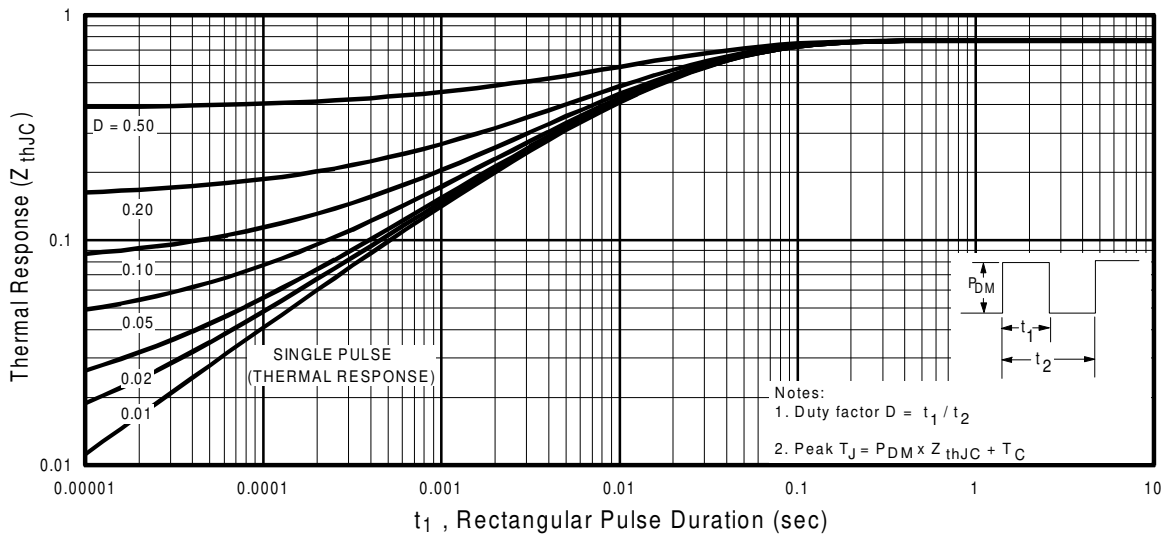
**Fig. 3 - Typical Transfer Characteristics**



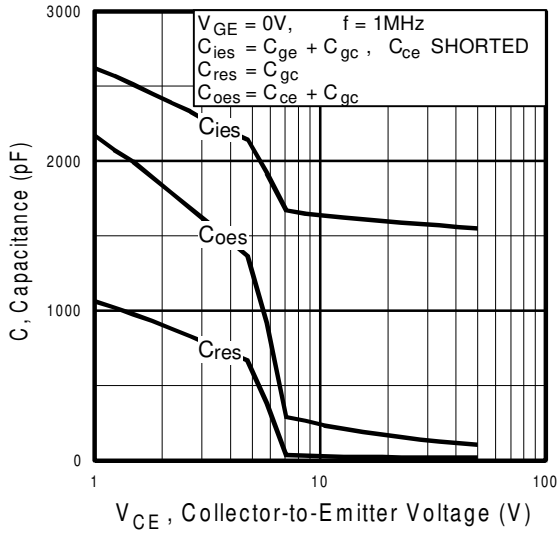
**Fig. 4 - Maximum Collector Current vs. Case Temperature**



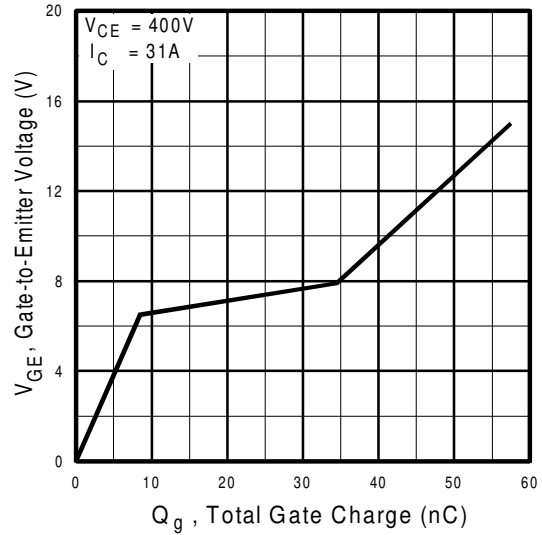
**Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature**



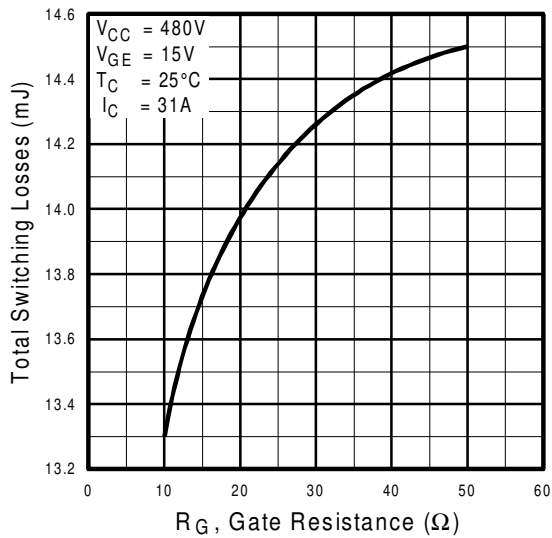
**Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



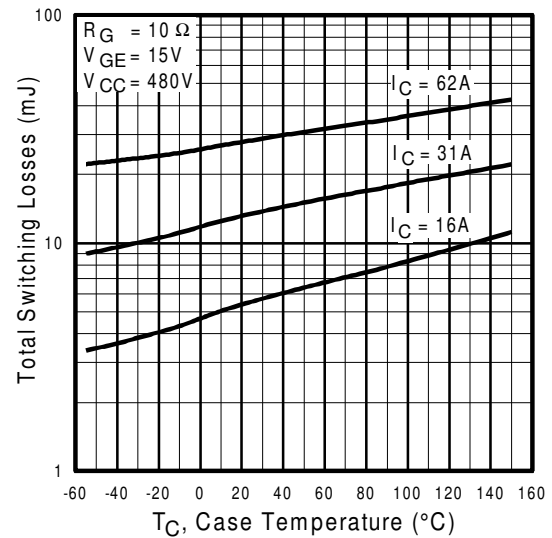
**Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage**



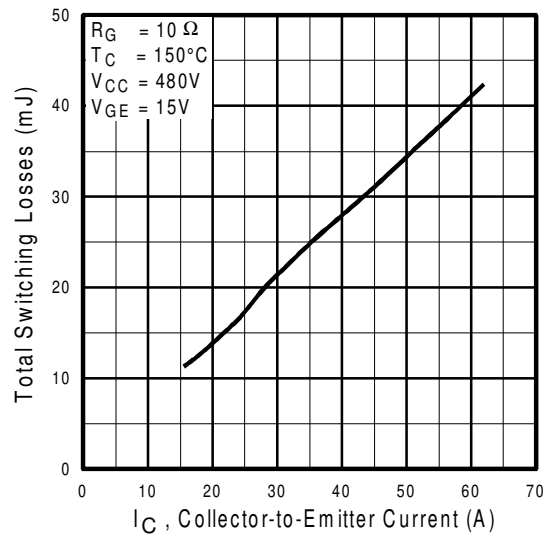
**Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage**



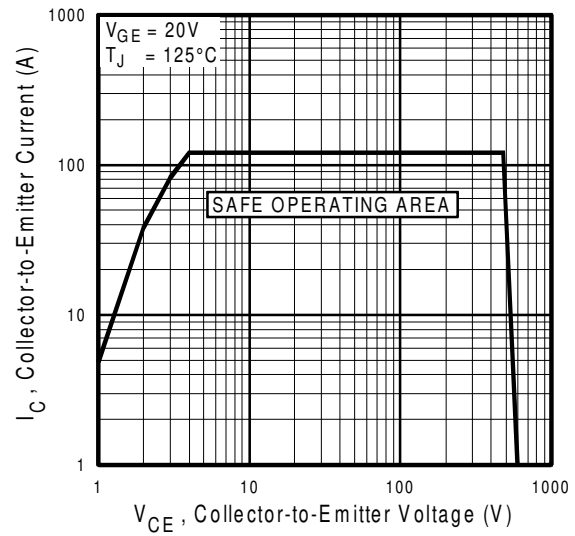
**Fig. 9 - Typical Switching Losses vs. Gate Resistance**



**Fig. 10 - Typical Switching Losses vs. Case Temperature**



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



**Fig. 12** - Turn-Off SOA

Refer to Section D for the following:

**Appendix C: Section D - page D-5**

- Fig. 13a - Clamped Inductive Load Test Circuit
- Fig. 13b - Pulsed Collector Current Test Circuit
- Fig. 14a - Switching Loss Test Circuit
- Fig. 14b - Switching Loss Waveform

**Package Outline 1 - JEDEC Outline TO-220AB**

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